

Citations for Target : Si₃N₄

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1973	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. 'Ranges and Distributions of Ions Implanted into Dielectrics' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 225-41 (1973)</i> <i>Comment : R,dR. (140-300 keV) Zn, Ga, As, Se, Cd, Te, Zn -> Si, Si₃N₄, Al₂O₃</i>	1973-Chu 2 0539
1973	Combasson, J. L. Bernard, J. Guernet, G. 'Physical Profile Measurements in Insulating Layers using the Ion Analyzer' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 285-94 (1973)</i> <i>Comment : R,dR. 60, 100 keV B -> SiO₂; 20, 40 keV B -> Si₃N₄; 60 keV B -> Si (Amorphous)</i>	1973-Comb 0537
1975	Ziegler, J. F. Chu, W. K. Feng, J. S. 'Empirical Corrections to the Energy Loss of 4He Ions in Oxides' <i>Appl. Phys. Letters, 27, 387-90 (1975)</i> <i>Comment : S. 2 MeV He -> Fe₂O₃, Fe₃O₄, MgO, Al₂O₃, SiO₂, Si₃N₄ All Rel. To Metal</i>	1975-Zieg 0880
1976	Ziegler, J. F. Chu, W. K. Feng, J. S. 'Evidence of Solid State Effects in the Energy Loss of 4He Ions in Matter' <i>Meyer, G. Linker and F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 15-27 (1976)</i> <i>Comment : S. 2 MeV He -> Fe₂O₃, Fe₃O₄, MgO, Al₂O₃, SiO₂, Si₃N₄</i>	1976-Zieg2 0851
1979	Doyle, B. L. Peercy, P. S. 'Technique for Profiling 1H with 2.5 MeV van de Graaff Accelerators.' <i>Appl. Phys. Letters, 34, 811-813 (1979)</i> <i>Comment : R. 1-3 MeV H -> Si₃N₄, Si</i>	1979-Doyl 1135
1979	Muller, G. Trapp, M. Schimko, R. Richter, C. E. 'Measurement of Range Distributions of Zinc and Nitrogen Ions in Multiple-Layer Substrates with Secondary Ion Microprobe' <i>Phys. Stat. Sol. A, 51, 87-92 (1979)</i> <i>Comment : R, dR. 50-300 keV N, Zn -> SiO₂-GaAs(I-X)P(X), SiO₂-Si₃N₄</i>	1979-Mull 1237